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Vishay Siliconix

# Automotive P-Channel 30 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY				
V <sub>DS</sub> (V)	-30			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.065			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.100			
I <sub>D</sub> (A)	-6.8			
Configuration	Single			

#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % Rg and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



ROHS COMPLIANT HALOGEN FREE

(4) S
(3) G
<b>८</b> (1, 2, 5, 6) D
P-Channel MOSFET

ORDERING INFORMATION	
Package	TSOP-6
Lead (Pb)-free and halogen-free	SQ3457CEV (for detailed order number please see <a href="https://www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	-30	V	
Gate-Source Voltage		V <sub>GS</sub> ± 20		V	
Continuous Drain Current	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	-6.8		
	T <sub>C</sub> = 125 °C		-3.9		
Continuous Source Current (Diode Conduction)		Is	-6.3	Α	
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	-27		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	-14		
Single Pulse Avalanche Energy	L = 0.1 111111	E <sub>AS</sub>	10	mJ	
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	5	W	
	T <sub>C</sub> = 125 °C		1.7		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount b	R <sub>thJA</sub>	110	°C/W	
Junction-to-Foot (Drain)		R <sub>thJF</sub>	30		

#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%$
- b. When mounted on 1" square PCB (FR-4 material)



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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = -250 μA		-30	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = -250 \mu A$		-2.0	-2.5		
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
Zero Gate Voltage Drain Current		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -30 V	-	-	-1		
	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -30 V, T <sub>J</sub> = 125 °C	-	-	-50	μΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -30 V, T <sub>J</sub> = 175 °C	-	-	-150		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = -10 V	$V_{DS} \ge 5 V$	-10	-	-	Α	
Paris Os and Os Olds Parists	Б	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -6 A	-	0.041	0.065		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -4.9 A	-	0.083	0.100	Ω	
Forward Transconductanceb	9fs	V <sub>DS</sub> = -15 V, I <sub>D</sub> = -5 A		-	8	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>		V <sub>DS</sub> = -15 V, f = 1 MHz	-	591	705	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	145	180		
Reverse Transfer Capacitance	C <sub>rss</sub>	1		-	84	120		
Total Gate Charge <sup>c</sup>	Qg		V <sub>DS</sub> = -15 V, I <sub>D</sub> = -5 A	-	12.9	21	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = -10 V		-	2.6	-		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	]		-	3.1	-		
Gate Resistance	R <sub>g</sub>	f = 1 MHz		2	5.9	11	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>				9	14	- ns	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = -15 V, $R_L$ = 3 $\Omega$ $I_D$ $\cong$ -5 A, $V_{GEN}$ = -10 V, $R_g$ = 1 $\Omega$		-	4	8		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	20	30		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	6	9		
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	- 27	Α	
Forward Voltage	$V_{SD}$	I <sub>F</sub> = -1.6 A, V <sub>GS</sub> = 0		_	-0.79	-1.1	V	

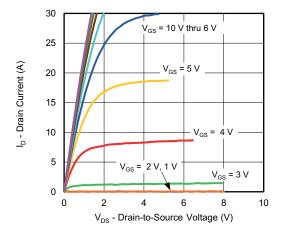
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

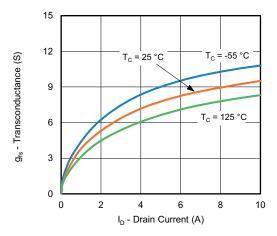
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



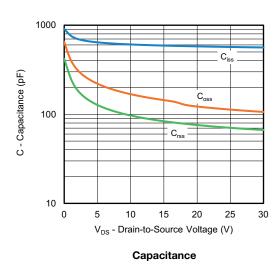
## TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)

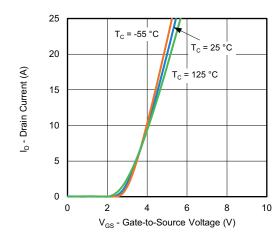


#### **Output Characteristics**

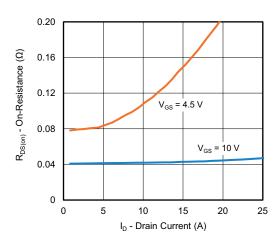


#### Transconductance

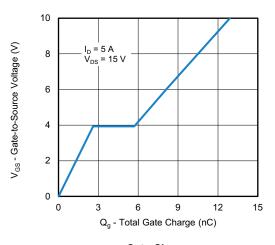




**Transfer Characteristics** 

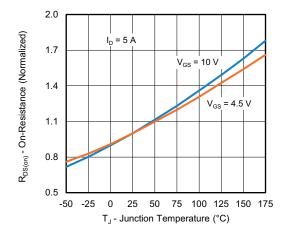


On-Resistance vs. Drain Current

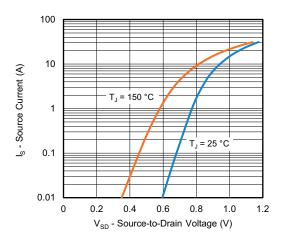




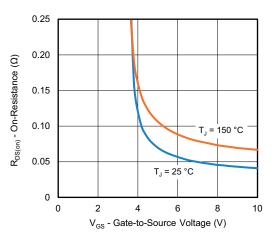
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



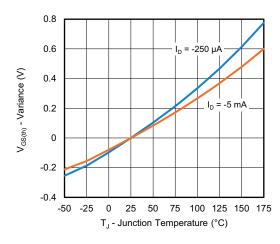
On-Resistance vs. Junction Temperature



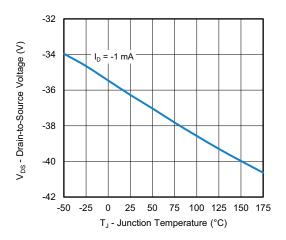
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



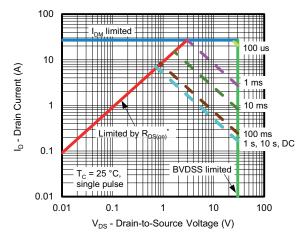
**Threshold Voltage** 



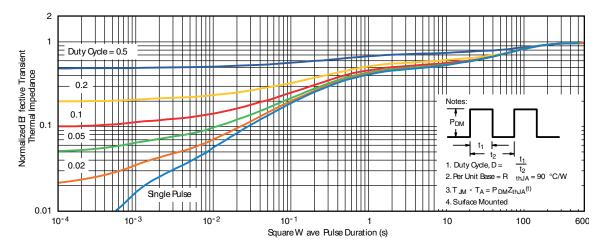
Drain Source Breakdown vs. Junction Temperature



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



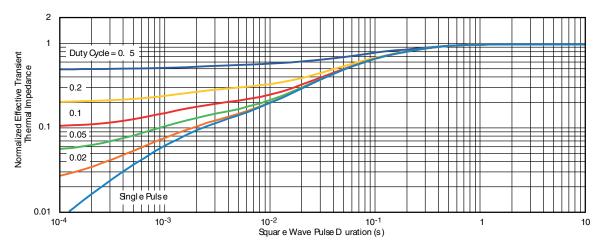
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
    Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

can widely vary depending on actual application parameters and operating conditions.

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and

reliability data, see www.vishay.com/ppg?61648.



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